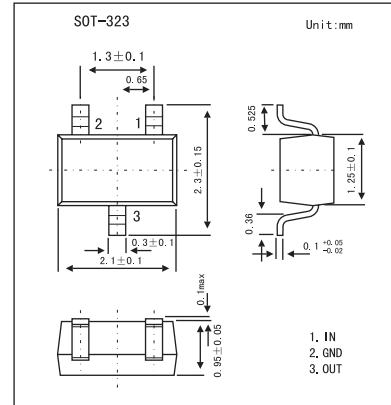


Schottky barrier diode

1PS70SB20

■ Features

- Ultra high switching speed
- Low forward voltage
- Guard ring protected
- Small SMD plastic package.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			40	V
Continuous forward current	I_F			500	mA
Non-repetitive peak forward current	I_{FSM}	$t = 8.3$ ms half sine wave; JEDEC method		2	A
Storage temperature	T_{stg}		-65	+150	$^\circ\text{C}$
Junction temperature	T_j			125	$^\circ\text{C}$
thermal resistance from junction to ambient	$R_{th\ j-a}$			500	K/W

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Max	Unit
Forward voltage	V_F	$I_F = 500$ mA		550	mV
Reverse current	I_R	$V_R = 35$ V		100	μ A
		$V_R = 35$ V; $T_j = 100$ $^\circ\text{C}$; Note 1		10	mA
Diode capacitance	C_d	$f = 1$ MHz; $V_R = 0$;	60	90	pF

Note

1. Pulse test: $t_p < 300$ μ s; $\delta \leq 0.02$.
2. Refer to SOT323(SC-70) Standard mounting conditions.

■ Marking

Marking	72
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